

# isc N-Channel MOSFET Transistor

# IXTY1R6N50P

### • FEATURES

- Static drain-source on-resistance:
   R<sub>DS</sub>(on) ≤ 6.5Ω
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATION

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

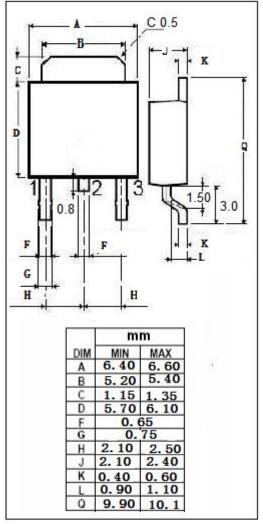
# pin 1.Gate 2.Drain 3.Source TO-252 package

## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                      | VALUE   | UNIT          |
|------------------|--------------------------------|---------|---------------|
| V <sub>DSS</sub> | Drain-Source Voltage           | 500     | V             |
| V <sub>G</sub> s | Gate-Source Voltage            | ±30     | V             |
| l <sub>D</sub>   | Drain Current-Continuous       | 1.6     | А             |
| Ірм              | Drain Current-Single Pulsed    | 2.5     | А             |
| P <sub>D</sub>   | Total Dissipation @Tc=25℃      | 43      | W             |
| Tj               | Operating Junction Temperature | -55~150 | ${\mathbb C}$ |
| T <sub>stg</sub> | Storage Temperature            | -55~150 | $^{\circ}$ C  |

# • THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                           | MAX  | UNIT |
|----------------------|-------------------------------------|------|------|
| R <sub>th(j-c)</sub> | Junction-to-case thermal resistance | 2.91 | °C/W |





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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | MAX  | UNIT       |
|---------------------|--------------------------------|--|-----|------|------------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; ID =250 μ A   | 500 |      | ٧          |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; ID =250 μ A                                   | 3.0 | 5.5  | V          |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> = 0.8A                                      |     | 6.5  | Ω          |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V                                       |     | ±100 | nA         |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V                        |     | 5    | μ <b>А</b> |
|                     |                                | V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 125°C |     | 50   |            |
| V <sub>SD</sub>     | Diode forward voltage          | I <sub>F</sub> = 1.6A; V <sub>GS</sub> = 0V                                      |     | 1.5  | V          |



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